

General Description

The WSF2040 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSF2040 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Ab

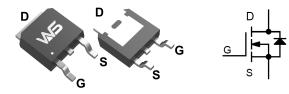
Product Summery

BVDSS	RDSON	ID
20V	6.2mΩ	45A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

TO-252 Pin Configuration



osolute Maximum Ratings					
Symbol	Parameter	Rating	Units		
V _{DS}	Drain-Source Voltage	20	V		
V _{GS}	Gate-Source Voltage	±12	V		
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ 10V	45	A		
I _D @T _C =100℃	Continuous Drain Current, V _{GS} @ 10V	28	A		
I _{DM}	Pulsed Drain Current	80	A		
EAS	Single Pulse Avalanche Energy	150	mJ		
I _{AS}	Avalanche Current	40	A		
P₀@T₀=25℃	Total Power Dissipation ⁴	60	W		
T _{STG}	Storage Temperature Range	-55 to 175	°C		
TJ	Operating Junction Temperature Range	-55 to 175	°C		

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient (Steady State)		62	°C/W
R _{θJC}	Thermal Resistance Junction-Case		4.0	°C/W



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N-Ch MOSFET

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	20			V
$\triangle BV_{DSS} / \triangle T_J$	BVDSS Temperature Coefficient	Reference to 25 $^\circ\!\!\mathrm{C}$, I_D=1mA		0.028		V/℃
Б	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =25A		6.2	8.5	mΩ
R _{DS(ON)}		V _{GS} =2.5V , I _D =10A		8.8	13	
V _{GS(th)}	Gate Threshold Voltage		0.4	0.70	1.1	V
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	— V _{GS} =V _{DS} , I _D =250uA		-6.16		mV/℃
	Drain-Source Leakage Current	V _{DS} =20V , V _{GS} =0V , T _J =25℃			1	uA
I _{DSS}		V _{DS} =20V , V _{GS} =0V , T _J =55℃			5	uA
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm20V$, $V_{DS}=0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =30A	10			S
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.0	3.1	Ω
Qg	Total Gate Charge (4.5V)	V _{DS} =10V , V _{GS} =4.5V , I _D =15A		19		
Q _{gs}	Gate-Source Charge			3.0		nC
Q _{gd}	Gate-Drain Charge			6.4		
T _{d(on)}	Turn-On Delay Time			10		
Tr	Rise Time	V _{DD} =10V , V _{GS} =10V ,		21		
T _{d(off)}	Turn-Off Delay Time	R _G =3.3Ω I _D =15A		39		- ns
T _f	Fall Time			19		
Ciss	Input Capacitance	V _{DS} =10V , V _{GS} =0V , f=1MHz		1450		
C _{oss}	Output Capacitance			238		pF
C _{rss}	Reverse Transfer Capacitance			212]

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current	$V_G=V_D=0V$, Force Current			30	А
V _{SD}	Diode Forward Voltage	V_{GS} =0V , I _S =1A , T _J =25 $^{\circ}$ C			1.2	V
t _{rr}	Reverse Recovery Time			25		nS
Qrr	Reverse Recovery Charge	IF=20A , dl/dt=100A/ μs , T $_{ m J}$ =25 $^\circ { m C}$		20		nC

Notes:

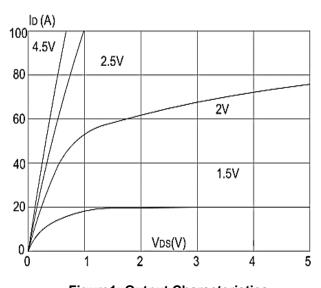
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition : Tj=25 $^{\circ}$ C ,V_{DD}=10V,V_{G}=10V,L=0.5mH,Rg=25\Omega,



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N-Ch MOSFET

Typical Characteristics



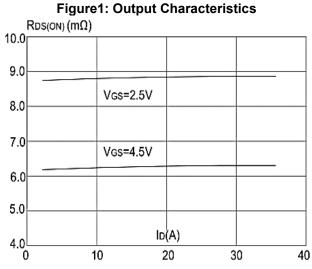
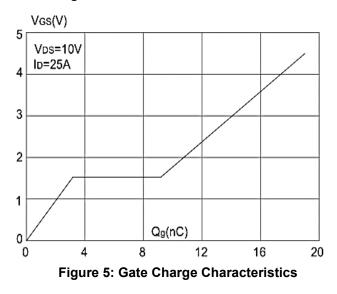
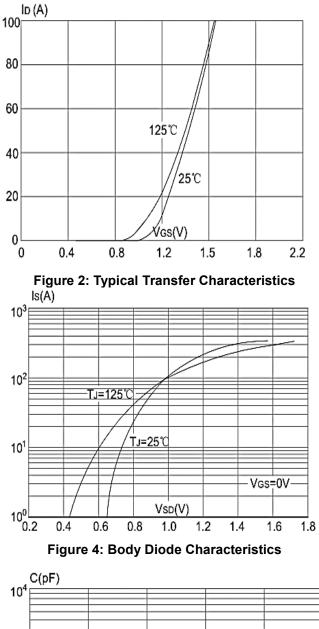


Figure 3:On-resistance vs. Drain Current





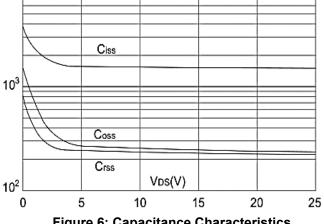


Figure 6: Capacitance Characteristics



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N-Ch MOSFET

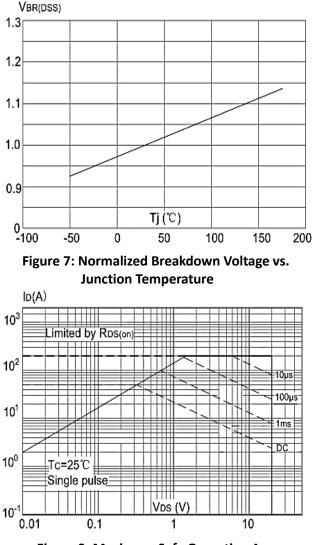


Figure 9: Maximum Safe Operating Area vs. Case Temperature

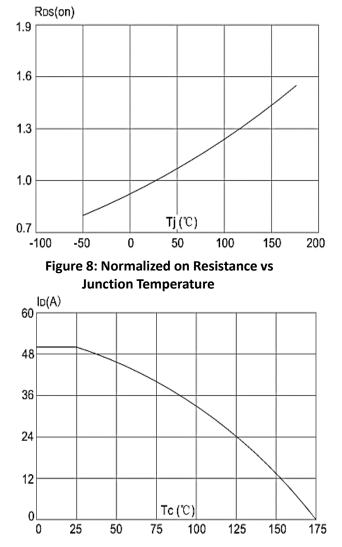
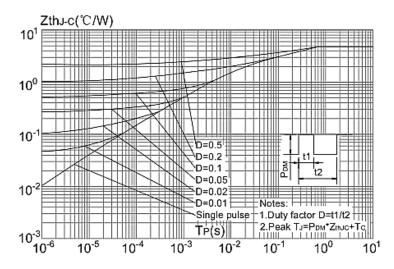
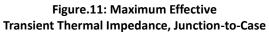


Figure 10: Maximum Continuous Drain Current







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